



THE DATASHEET OF BD743B-S

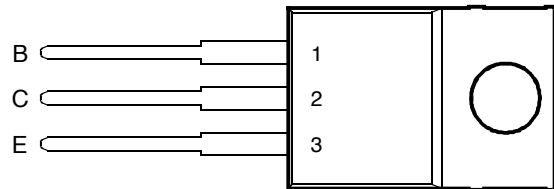


BD743, BD743A, BD743B, BD743C NPN SILICON POWER TRANSISTORS

BOURNS®

- Designed for Complementary Use with the BD744 Series
- 90 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- 20 A Peak Collector Current
- Customer-Specified Selections Available

TO-220 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRACA



This series is obsolete and not recommended for new designs.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BD743	V_{CBO}	50	V
	BD743A		70	
	BD743B		90	
	BD743C		110	
Collector-emitter voltage ($I_B = 0$)	BD743	V_{CEO}	45	V
	BD743A		60	
	BD743B		80	
	BD743C		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	15	A
Peak collector current (see Note 1)		I_{CM}	20	A
Continuous base current		I_B	5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	90	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	2	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	90	mJ
Operating free air temperature range		T_A	-65 to +150	°C
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	250	°C

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.72 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 0.4$ A, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002
 Specifications are subject to change without notice.

BD743, BD743A, BD743B, BD743C

NPN SILICON POWER TRANSISTORS

BOURNS®

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$	$I_B = 0$	(see Note 5)	BD743 BD743A BD743B BD743C	45 60 80 100		V
I_{CBO} Collector cut-off current	$V_{CE} = 50 \text{ V}$ $V_{CE} = 70 \text{ V}$ $V_{CE} = 90 \text{ V}$ $V_{CE} = 110 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	$T_C = 125^\circ\text{C}$ $T_C = 125^\circ\text{C}$ $T_C = 125^\circ\text{C}$ $T_C = 125^\circ\text{C}$	BD743 BD743A BD743B BD743C		0.1 0.1 0.1 0.1	mA
I_{CEO} Collector cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 60 \text{ V}$	$I_B = 0$ $I_B = 0$		BD743/743A BD743B/743C		0.1 0.1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				0.5	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 1 \text{ A}$ $I_C = 5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)		40 20 5	150	
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 0.5 \text{ A}$ $I_B = 5 \text{ A}$	$I_C = 5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)			1 3	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 5 \text{ A}$ $I_C = 15 \text{ A}$	(see Notes 5 and 6)			1 3	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 1 \text{ A}$	$f = 1 \text{ kHz}$		25		
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = 10 \text{ V}$	$I_C = 1 \text{ A}$	$f = 1 \text{ MHz}$		5		

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.4	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_d Delay time	$I_C = 5 \text{ A}$ $V_{BE(off)} = -4.2 \text{ V}$	$I_{B(on)} = 0.5 \text{ A}$ $R_L = 6 \Omega$	$I_{B(off)} = -0.5 \text{ A}$ $t_p = 20 \mu\text{s}$, $dc \leq 2\%$		20		ns
t_r Rise time					350		ns
t_s Storage time					500		ns
t_f Fall time					400		ns

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

TYPICAL CHARACTERISTICS

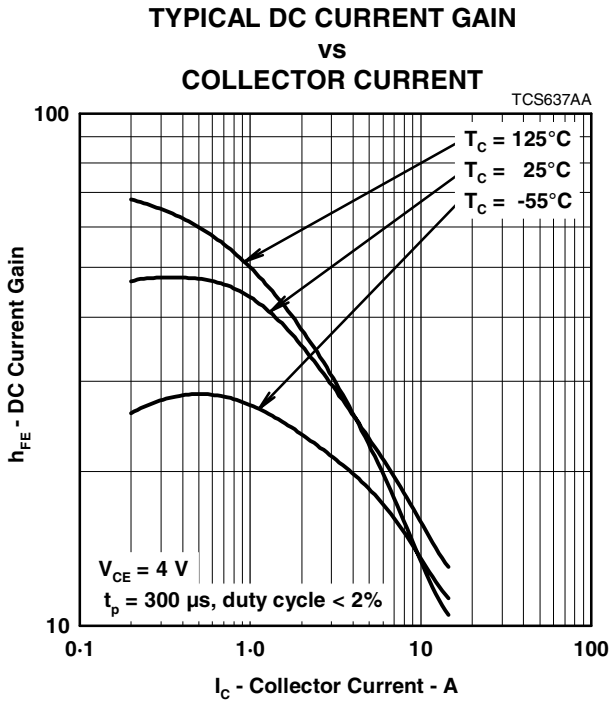


Figure 1.

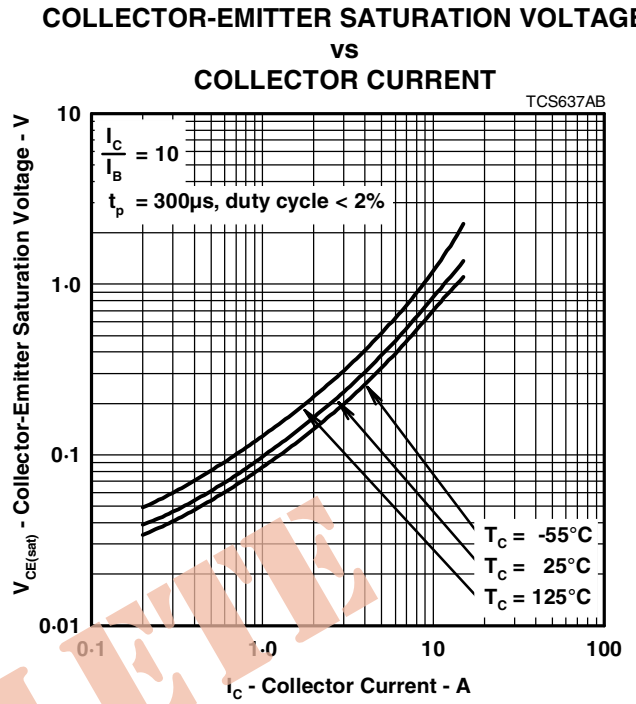


Figure 2.

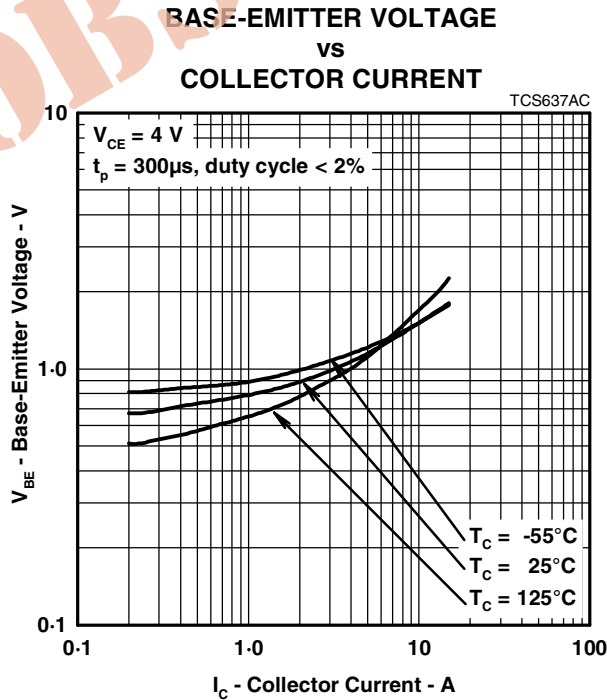


Figure 3.

PRODUCT INFORMATION

AUGUST 1978 - REVISED SEPTEMBER 2002
Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS

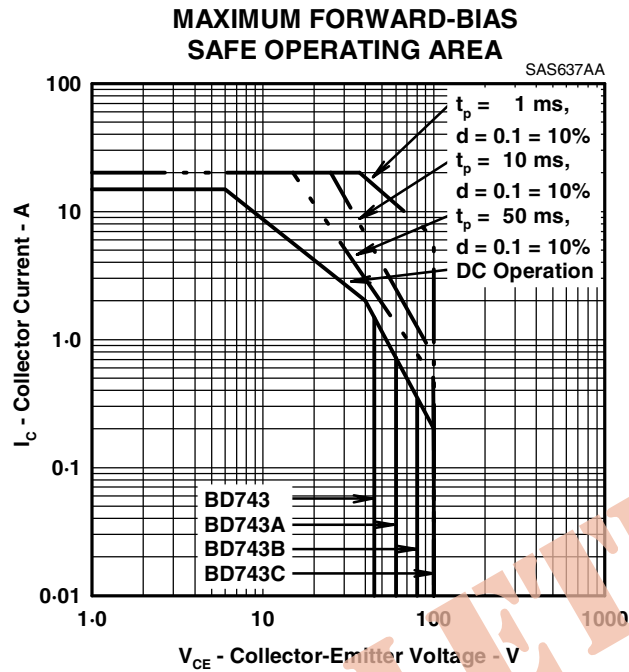


Figure 4.

THERMAL INFORMATION

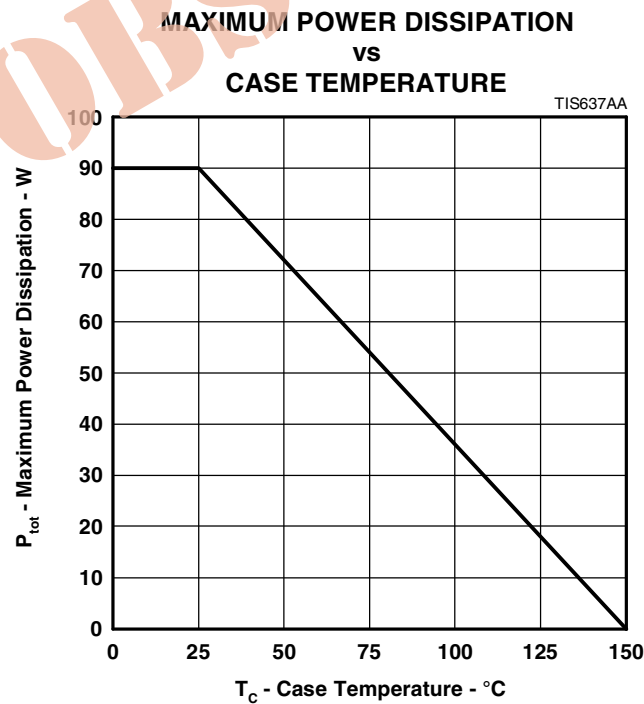




Figure 5.

PRODUCT INFORMATION

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View BD743B-S on WIN SOURCE](#)
-  [Bourns Inc. Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management